

Sub E
C1
Cont.
a first isolation region which isolates the MOS transistor from other MOS transistors on the semiconductor substrate;

a second isolation region formed between the MOS transistor and the first isolation region;

a silicide layer formed on a surface of the semiconductor substrate excluding the first and second isolation regions;

a second diffusion region which is formed in a region isolated by the second isolation region from the MOS transistor and makes up a lateral bipolar transistor together with a well in the semiconductor substrate and the first diffusion region of the MOS transistor; and

a third diffusion region which is formed at a deeper position of the first diffusion region near the second isolation region and makes up a Zener diode by the PN junction together with the first diffusion region of the MOS transistor.

Sub E
C2
20. (Amended) A semiconductor device comprising:
a semiconductor substrate;
a MOS transistor which is formed on the semiconductor substrate and includes a first diffusion region;

a first isolation region which isolates the MOS transistor from other MOS transistors on the semiconductor substrate;

a second isolation region formed between the MOS transistor and the first isolation region;

a second diffusion region which is formed in a region isolated by the second isolation region from the MOS transistor and makes up a lateral bipolar transistor together with a well in the semiconductor substrate and the first diffusion region of the MOS transistor;